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# IGBT 600V, 14A, N-Channel

#### **Features**

- Reverse Conducting II IGBT
- IGBT V<sub>CE</sub>(sat)=1.85V typ. (I<sub>C</sub>=15A, V<sub>GE</sub>=15V)
- IGBT tf=75ns typ.
- Diode V<sub>F</sub>=1.7V typ. (I<sub>F</sub>=15A)
- Diode t<sub>rr</sub>=95ns typ.
- 10µs Short Circuit Capability

### **Applications**

• General Purpose Inverter

## **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C, Unless otherwise specified

Parameter		Symbol	Value	Unit
Collector to Emitter Voltage		VCES	600	V
Gate to Emitter Voltage		VGES	±20	٧
Collector Current (DC)	@Tc=25°C *2		24	Α
Limited by Tjmax	@Tc=100°C *2	IC *1	14	А
Collector Current (Peak)		ICP	60	Α
Pulse width Limited by Tjmax  Diode Average Output Current		lo	15	A
Power Dissipation  Tc=25°C (Our ideal heat dissipation condition) *2		PD	54	W
Junction Temperature	Tj	175	°C	
Storage Temperature		Tstg	–55 to +175	°C

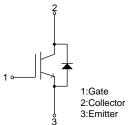
Note: \*1 Collector Current is calculated from the following formula.

$$I_{C}(\text{Tc}) = \frac{\text{Tjmax - Tc}}{\text{R}_{th}(\text{j-c}) \times \text{V}_{CE}(\text{sat}) (I_{C}(\text{Tc}))}$$

\*2 Our condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminum.

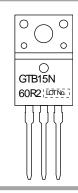
#### Electrical Connection N-Channel





TO-220F-3FS

#### Marking



Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

#### **Electrical Characteristics** at Ta = 25°C, Unless otherwise specified

Daramatar	0	Conditions		Value			11.2
Parameter	Symbol			min	typ	max	Unit
Collector to Emitter Breakdown Voltage	V(BR)CES	I <sub>C</sub> =500μA, V <sub>GE</sub> =0V		600			V
Collector to Emitter Cut off Current	ICES	V <sub>CE</sub> =600V, V <sub>GE</sub> =0V	Tc=25°C			10	μΑ
			Tc=125°C			1	mA
Gate to Emitter Leakage Current	IGES	V <sub>GE</sub> =±20V, V <sub>CE</sub> =0V				±100	nA
Gate to Emitter Threshold Voltage	V <sub>GE</sub> (th)	V <sub>CE</sub> =20V, I <sub>C</sub> =250μA		4.5		7.0	٧
Collector to Emitter Saturation Voltage		V <sub>GE</sub> =15V, I <sub>C</sub> =15A	Tc=25°C		1.85	2.1	V
	VCE(sat)	V <sub>GE</sub> =15V, I <sub>C</sub> =14A	Tc=100°C		2.0	2.3	٧
Forward Diode Voltage	٧F	I <sub>F</sub> =15A			1.7	2.1	V
Input Capacitance	Cies				2000		pF
Output Capacitance	Coes	V <sub>CE</sub> =20V, f=1MHz			65		pF
Reverse Transfer Capacitance	Cres				50		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	V <sub>CC</sub> =300V, I <sub>C</sub> =15A R <sub>G</sub> =30Ω, L=500μH			70		ns
Rise Time	t <sub>r</sub>				40		ns
Turn-ON Time	ton				200		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	V <sub>GE</sub> =0V/15V		190		ns	
Fall Time	tf	Vclamp=400V Tc=25°C See Fig.1, See Fig.2			75		ns
Turn-OFF Time	toff				290		ns
Turn-ON Energy	Eon				550		μJ
Turn-OFF Energy	Eoff				220		μJ
Total Gate Charge	Qg	V <sub>CE</sub> =300V, V <sub>GE</sub> =15V, I <sub>C</sub> =15A			80		nC
Gate to Emitter Charge	Qge				16		nC
Gate to Collector "Miller" Charge	Qgc				38		nC
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =15A,di/dt=300A/μs, V <sub>C</sub>	C=300V, See Fig.3		95		ns

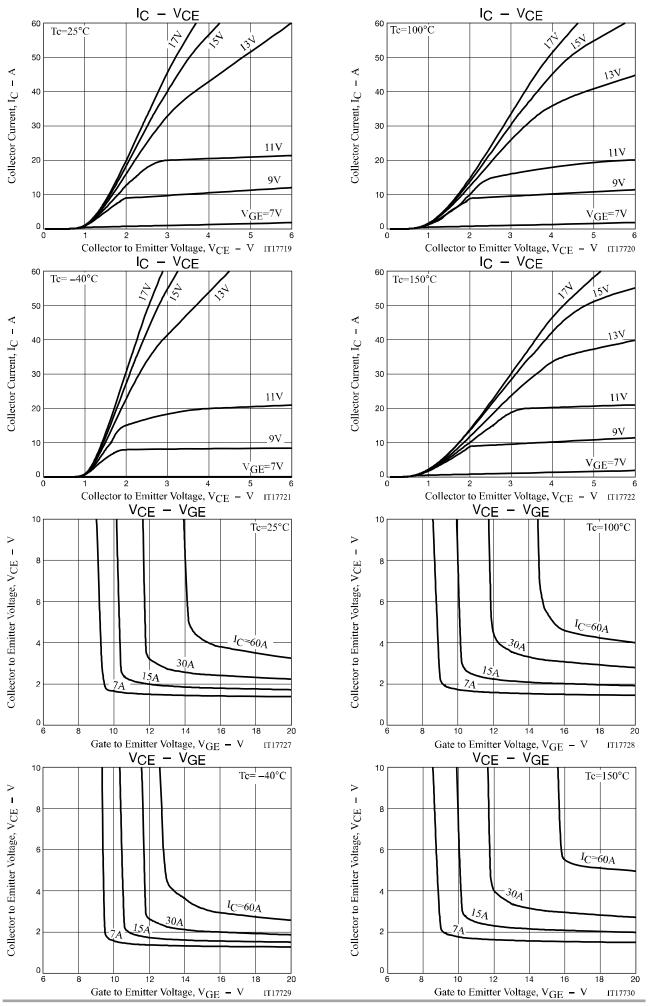
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

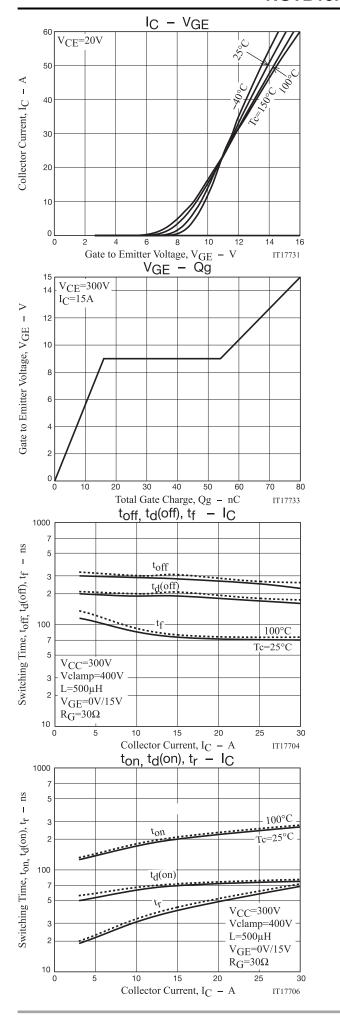
#### Thermal Characteristics at Ta = 25°C, Unless otherwise specified

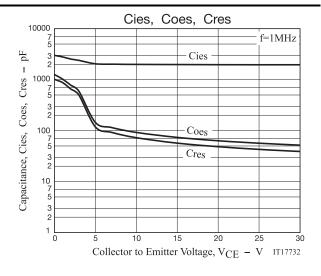
Parameter	Symbol	Conditions	Value	Unit
Thermal Resistance IGBT (Junction to Case)	Rth(j-c) (IGBT)	Tc=25°C (Our ideal heat dissipation condition) *2	2.78	°C/W
Thermal Resistance (Junction to Ambient)	Rth(j-a)		69	°C/W

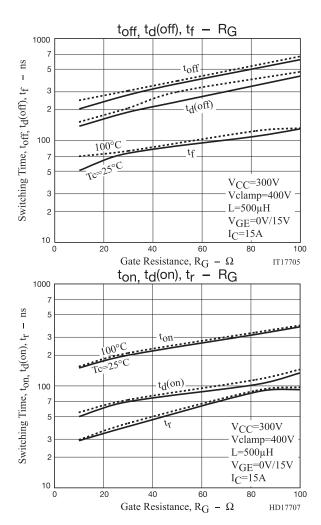
Note: \*2 Our condition is radiation from backside.

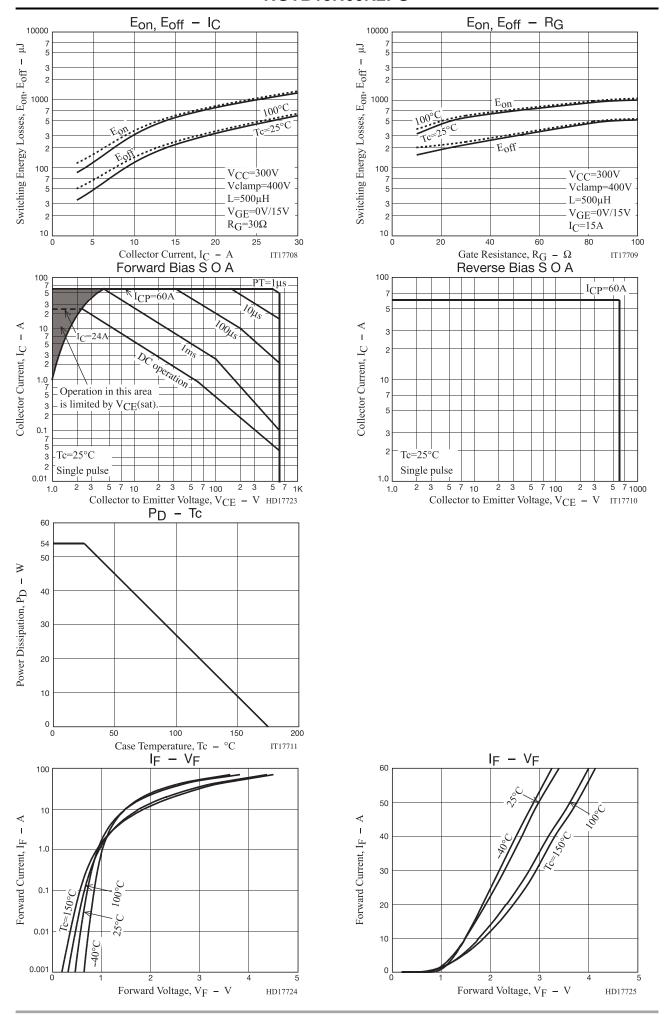
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminum.











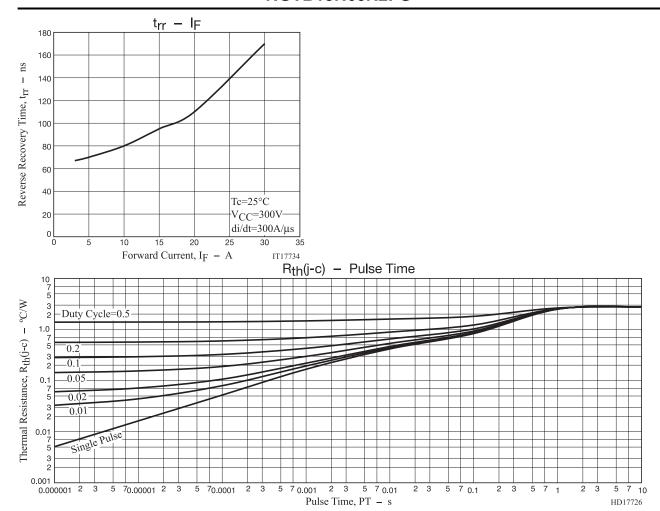


Fig.1 Switching Time Test Circuit

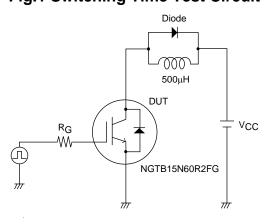


Fig.2 Timing Chart

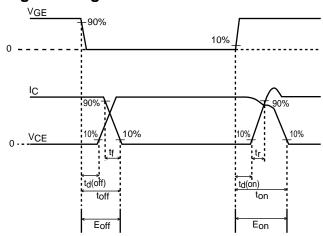
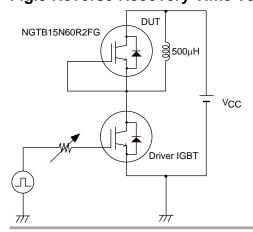


Fig.3 Reverse Recovery Time Test Circuit



#### **Package Dimensions**

NGTB15N60R2FG

#### TO-220F-3FS

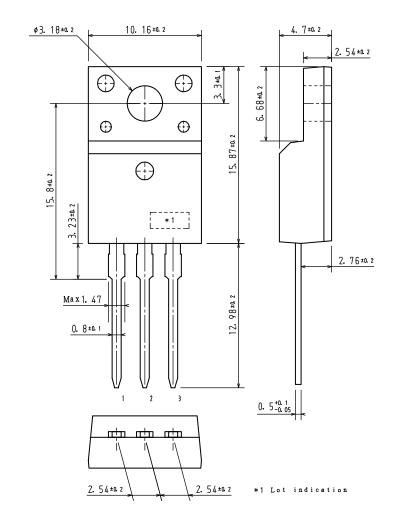
CASE 221AM ISSUE O

unit: mm

1:Gate

2:Collector

3:Emitter



#### **ORDERING INFORMATION**

Device	Package	Shipping	note
NGTB15N60R2FG	TO-220F-3FS	50 pcs. / tube	Pb-Free and Halogen Free

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